



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

ATP101 — General-Purpose Switching Device Applications

Features

- Low ON-resistance
- Slim package
- Halogen free compliance
- Large current
- 4.5V drive
- Protection diode in

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-30	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		-25	A
Drain Current (PW≤10μs)	I _{DP}	PW≤10μs, duty cycle≤1%	-75	A
Allowable Power Dissipation	P _D	Tc=25°C	30	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E _{AS}		25	mJ
Avalanche Current *2	I _{AV}		-13	A

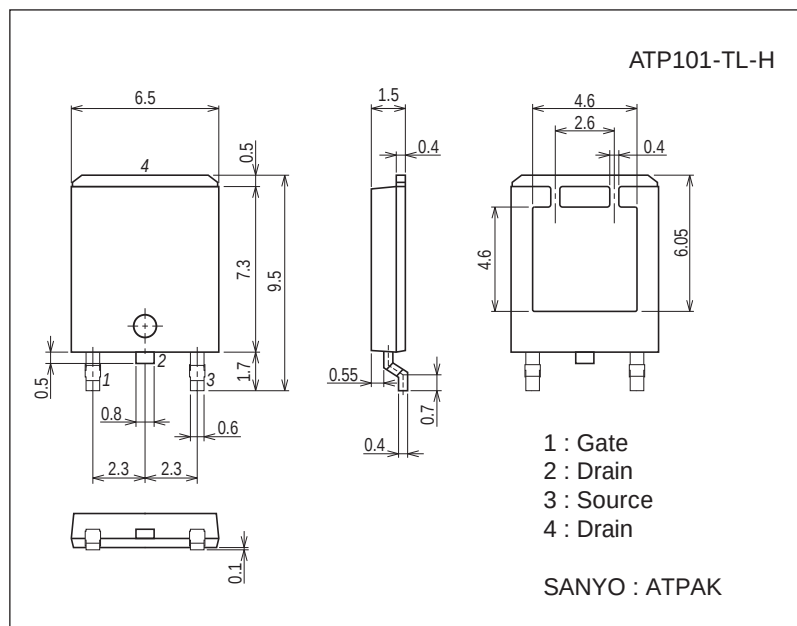
Note : *1 V_{DD}=-10V, L=200μH, I_{AV}=-13A

*2 L≤200μH, Single pulse

Package Dimensions

unit : mm (typ)

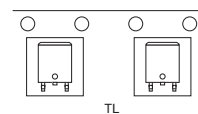
7057-001



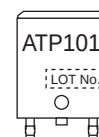
Product & Package Information

- Package : ATPAK
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

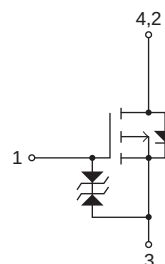
Packing Type: TL



Marking



Electrical Connection

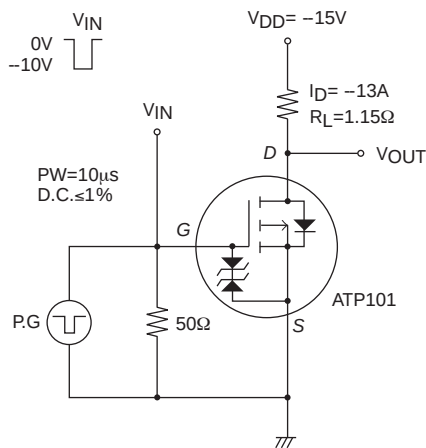


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Electrical Characteristics at Ta=25°C

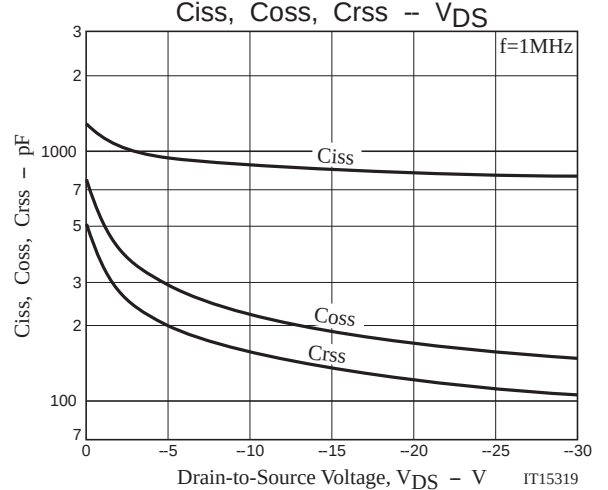
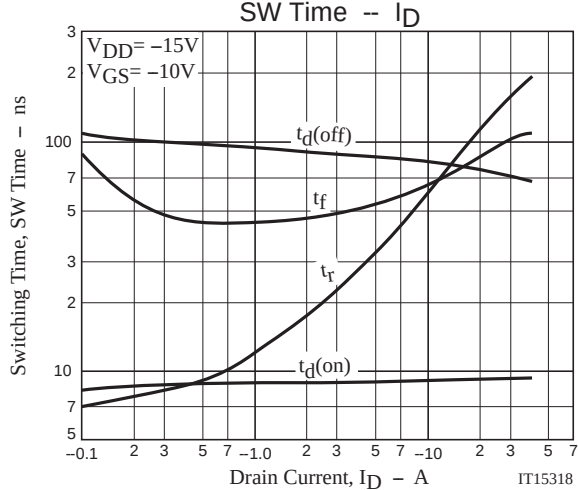
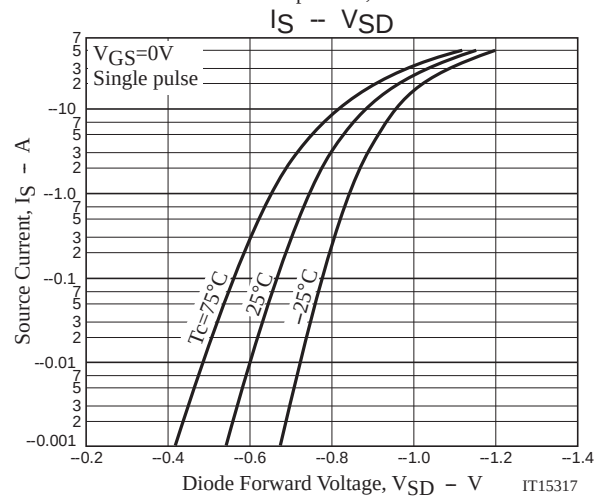
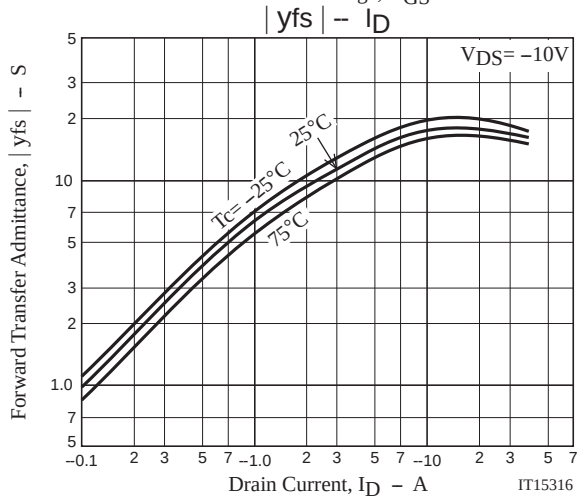
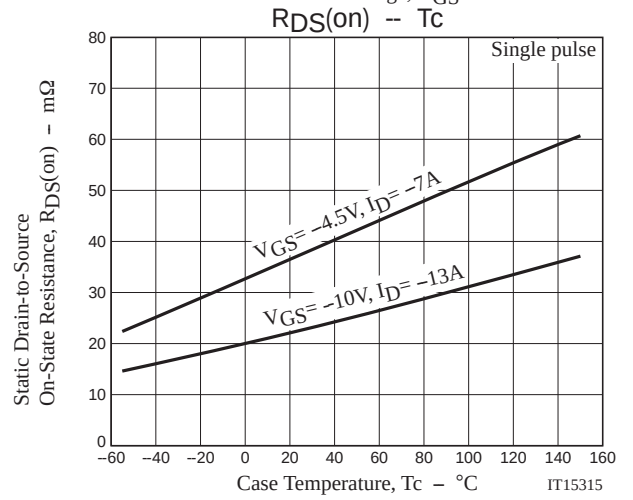
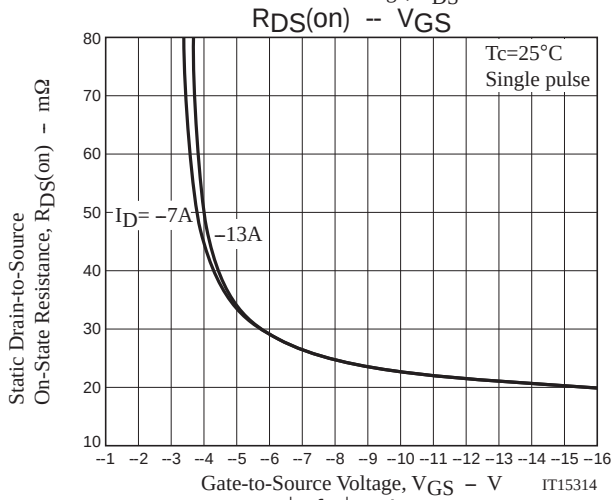
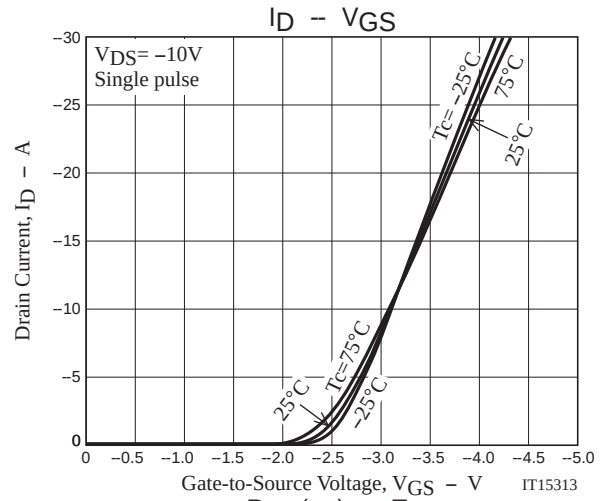
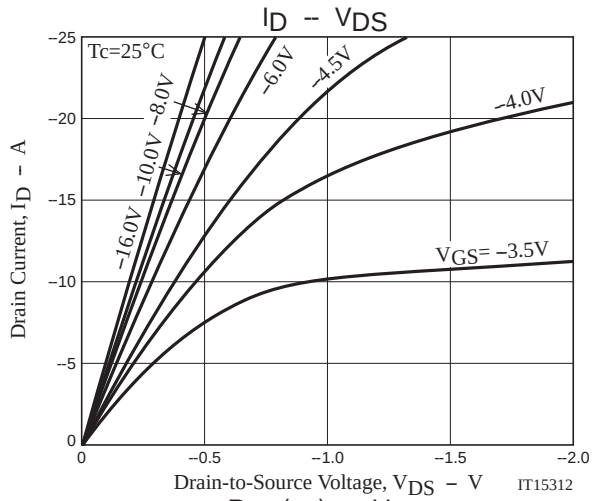
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0V$	-30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0V$			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 16V, V_{DS} = 0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.2		-2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -10V, I_D = -13A$		17		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D = -13A, V_{GS} = -10V$		23	30	$m\Omega$
	$R_{DS(on)2}$	$I_D = -7A, V_{GS} = -4.5V$		36	51	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS} = -10V, f = 1MHz$		875		pF
Output Capacitance	C_{oss}			220		pF
Reverse Transfer Capacitance	C_{rss}			155		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		9.2		ns
Rise Time	t_r			70		ns
Turn-OFF Delay Time	$t_{d(off)}$			80		ns
Fall Time	t_f			70		ns
Total Gate Charge	Q_g	$V_{DS} = -15V, V_{GS} = -10V, I_D = -25A$		18.5		nC
Gate-to-Source Charge	Q_{gs}			3.2		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			4.0		nC
Diode Forward Voltage	V_{SD}	$I_S = -25A, V_{GS} = 0V$		-0.99	-1.5	V

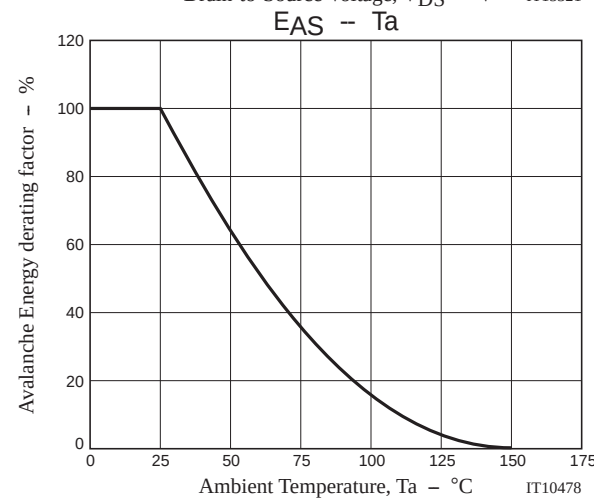
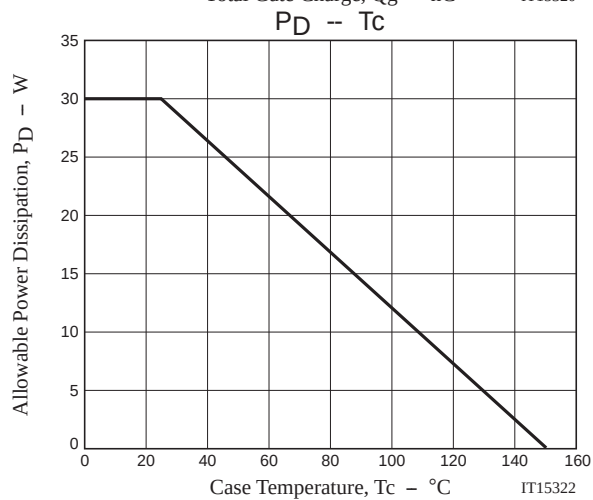
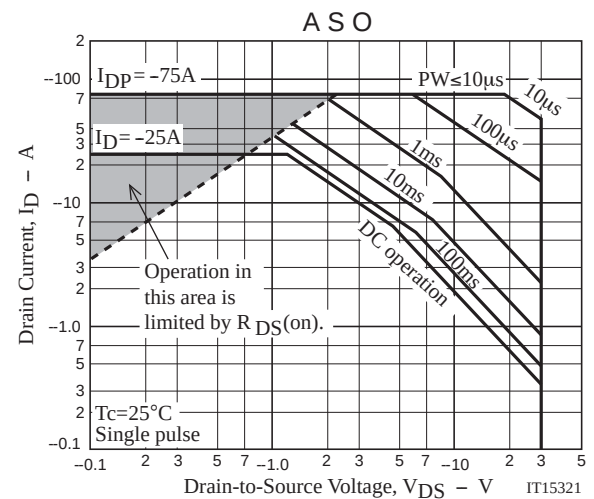
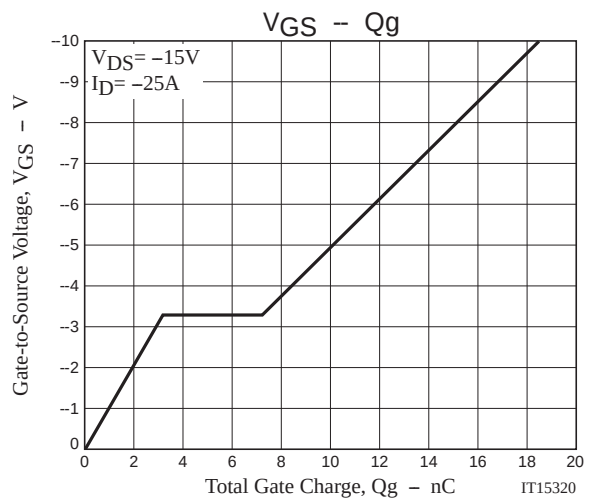
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
ATP101-TL-H	ATPAK	3,000pcs./reel	Pb Free and Halogen Free

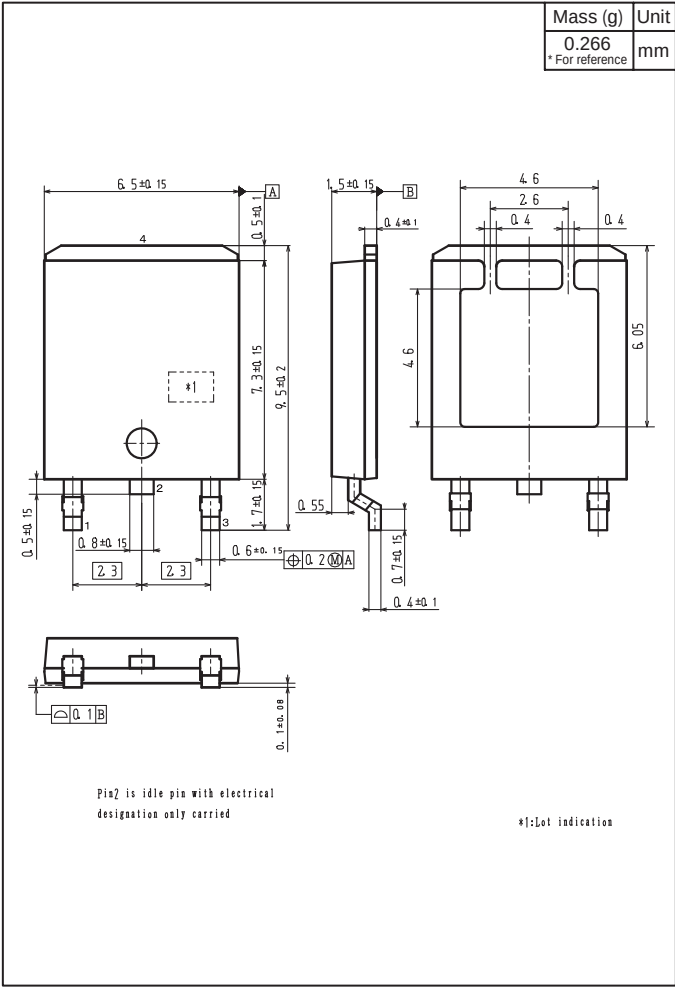




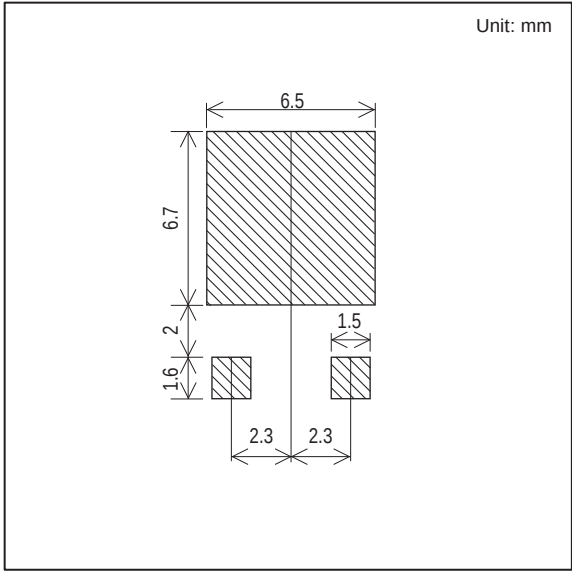
ATP101

Outline Drawing

ATP101-TL-H



Land Pattern Example



Note on usage : Since the ATP101 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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